NCE P-Channel Super Trench Power MOSFET

Description

The NCEP15P30AK uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS(ON)}}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

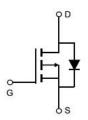
General Features

- V_{DS} =-150V, I_{D} =-29.5A $R_{DS(ON)}$ =90mΩ (typical) @ V_{GS} =-10V $R_{DS(ON)}$ =107mΩ (typical) @ V_{GS} =-4.5V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!







Schematic Diagram

Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|-------------|----------------|-----------|------------|----------|
| NCEP15P30AK | NCEP15P30AK | TO-252-2L | - | - | - |

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|--|-----------------------|------------|--------------|
| Drain-Source Voltage | V _{DS} | -150 | V |
| Gate-Source Voltage | Vgs | ±20 | V |
| Drain Current-Continuous | I _D | -29.5 | А |
| Drain Current-Continuous(T _C =100 °C) | I _D (100℃) | -20.6 | А |
| Pulsed Drain Current | I _{DM} | -118 | А |
| Maximum Power Dissipation | P _D | 235 | W |
| Derating factor | | 1.57 | W/℃ |
| Single pulse avalanche energy (Note 1) | E _{AS} | 207 | mJ |
| Operating Junction and Storage Temperature Range | T_{J}, T_{STG} | -55 To 175 | $^{\circ}$ C |

Thermal Characteristic

| Thermal Resistance, Junction-to-Case Rejc 0.64 C/W | | $R_{	heta JC}$ | | °C/W |
|--|--|----------------|--|------|
|--|--|----------------|--|------|

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Electrical Characteristics (Tc=25 $^{\circ}$ C unless otherwise noted)

| Parameter | Symbol | Condition | Min | Тур | Max | Unit |
|------------------------------------|---------------------|--|------|------|-------|------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V I _D =-250μA | -150 | - | - | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =-150V,V _{GS} =0V | - | - | -1 | μA |
| Gate-Body Leakage Current | I _{GSS} | V _{GS} =±20V,V _{DS} =0V | - | - | ±100 | nA |
| On Characteristics | | | • | | | |
| Gate Threshold Voltage | V _{GS(th)} | $V_{DS}=V_{GS}$, $I_{D}=-250\mu A$ | -1.2 | -1.7 | -2.5 | V |
| Drain-Source On-State Resistance | Б | V _{GS} =-10V, I _D =-15A | - | 90 | 105 | mΩ |
| Drain-Source On-State Resistance | R _{DS(ON)} | V _{GS} =-4.5V, I _D =-15A | - | 107 | 125 | mΩ |
| Forward Transconductance | g FS | V _{DS} =-5V,I _D =-15A | - | 30 | - | S |
| Dynamic Characteristics | | | • | | | |
| Input Capacitance | Clss | \\ 75\\\\ 0\\ | - | 1650 | - | PF |
| Output Capacitance | Coss | V_{DS} =-75 V , V_{GS} =0 V , | - | 135 | - | PF |
| Reverse Transfer Capacitance | Crss | F=1.0MHz | - | 12 | - | PF |
| Switching Characteristics (Note 2) | | | • | 1 | | |
| Turn-on Delay Time | t _{d(on)} | | - | 10 | - | nS |
| Turn-on Rise Time | t _r | V_{DD} =-50 V , I_{D} =-15 A | - | 18 | - | nS |
| Turn-Off Delay Time | t _{d(off)} | V_{GS} =-10 V , R_G =1.6 Ω | - | 20 | - | nS |
| Turn-Off Fall Time | t _f | | - | 15 | - | nS |
| Total Gate Charge | Qg | \/ 75\/ \ 45A | - | 25 | - | nC |
| Gate-Source Charge | Q _{gs} | V _{DS} =-75V,I _D =-15A, | - | 5.2 | - | nC |
| Gate-Drain Charge | Q_{gd} | V _{GS} =-10V | - | 3.1 | - | nC |
| Drain-Source Diode Characteristics | | | | | | |
| Diode Forward Voltage | V _{SD} | V _{GS} =0V,I _S =-15A | - | | -1.2 | V |
| Diode Forward Current | Is | | - | - | -29.5 | Α |
| Reverse Recovery Time | t _{rr} | T _J = 25°C, I _F =-15A | - | 55 | - | nS |
| Reverse Recovery Charge | Qrr | di/dt = 100A/µs | - | 101 | - | nC |
| | | | | | | |

Notes:

- 1. EAS condition : Tj=25 $^{\circ}\text{C}$,VDD=-50V,VG=-10V,L=0.5mH,Rg=25 Ω
- 2. Guaranteed by design, not subject to production
- 3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of TJ(MAX)=175°C. The SOA curve provides a single pulse rating.





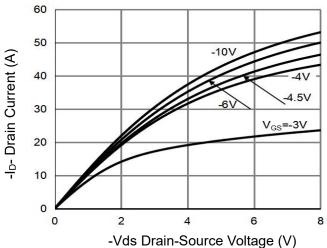


Figure 1 Output Characteristics

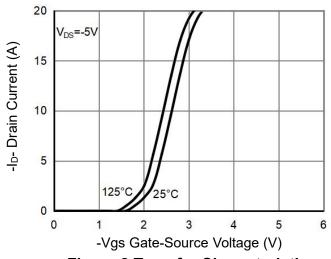


Figure 2 Transfer Characteristics

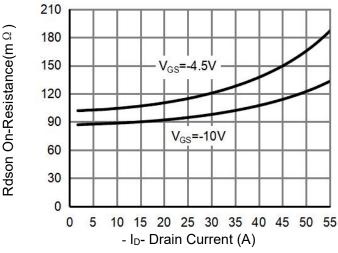


Figure 3 Rdson- Drain Current

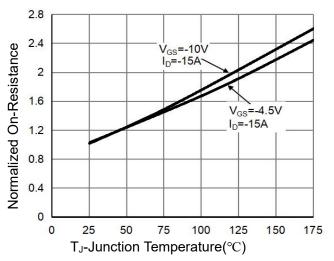


Figure 4 Rdson-JunctionTemperature

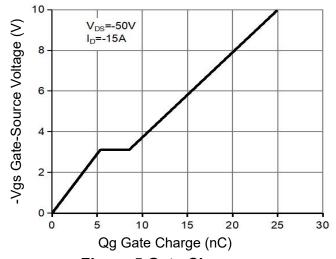


Figure 5 Gate Charge

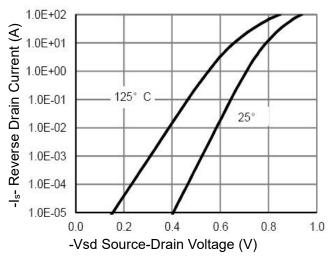


Figure 6 Source- Drain Diode Forward

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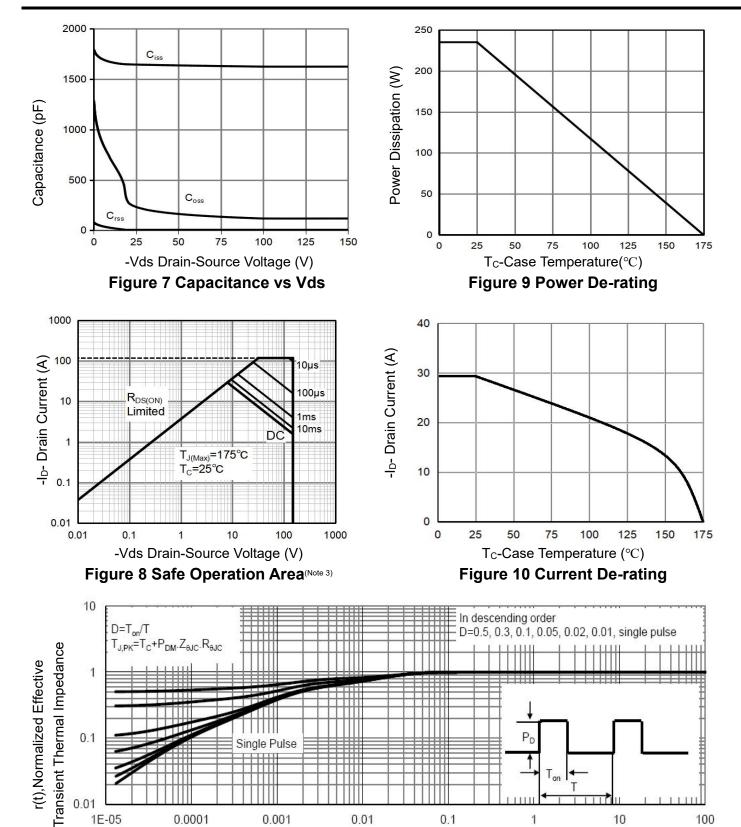
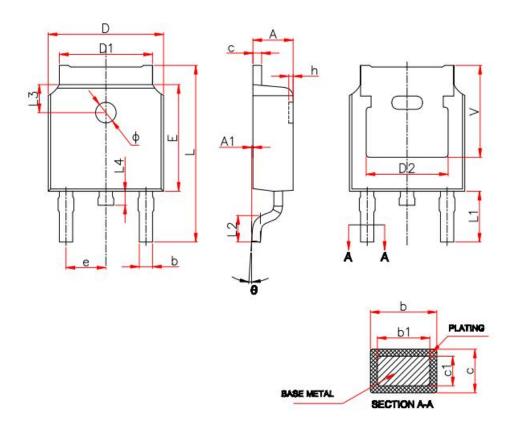


Figure 11 Normalized Maximum Transient Thermal Impedance

Square Wave Pluse Duration(sec)



TO-252-2L Package Information



| Cumbal | Millimeters | | |
|----------|-------------|-------|--|
| Symbol - | Min. | Max. | |
| Α | 2.20 | 2.40 | |
| A1 | 0.00 | 0.13 | |
| b | 0.66 | 0.86 | |
| b1 | 0.73 | 0.79 | |
| С | 0.46 | 0.58 | |
| c1 | 0.50 | 0.52 | |
| D | 6.50 | 6.70 | |
| D1 | 5.10 | 5.46 | |
| D2 | 4.83 REF. | | |
| E | 6.00 | 6.20 | |
| е | 2.19 | 2.39 | |
| L | 9.80 | 10.40 | |
| L1 | 2.90 REF. | | |
| L2 | 1.40 | 1.70 | |
| L3 | 1.60 | REF. | |
| L4 | 0.60 | 1.00 | |
| Ф | 1.10 | 1.30 | |
| θ | 0° 8° | | |

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